2SA1700



# **High-Voltage Driver Applications**

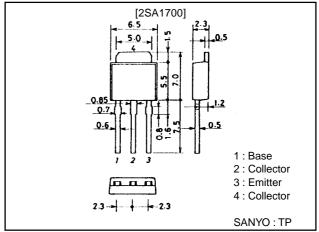
#### **Features**

- · High breakdown voltage.
- · Adoption of MBIT process.
- · Excellent hFE linearity.

### **Package Dimensions**

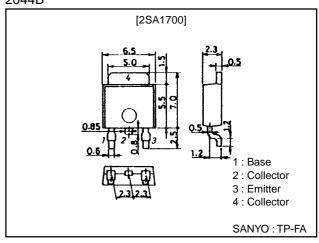
unit:mm

2045B



unit:mm

### 2044B



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# **Specifications**

### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V <sub>CBO</sub>		-400	V
Collector-to-Emitter Voltage	V <sub>CEO</sub>		-400	V
Emitter-to-Base Voltage	V <sub>EBO</sub>		-5	V
Collector Current	IC		-200	mA
Colletor Current (Pulse)	I <sub>CP</sub>		-400	mA
Collector Dissipation	PC		1	W
		Tc=25°C	10	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

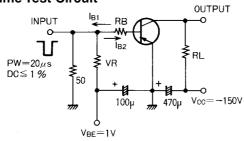
### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Uill
Collector Cutoff Current	ICBO	V <sub>CB</sub> =-300V, I <sub>E</sub> =0			-0.1	μΑ
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =-4V, I <sub>C</sub> =0			-0.1	μA
DC Current Gain	hFE	V <sub>CE</sub> =-10V, I <sub>C</sub> =-50mA	60*		200*	
Gain-Bandwidth Product	fT	V <sub>CE</sub> =-30V, I <sub>C</sub> =-10mA		70		MHz
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-50mA, I <sub>B</sub> =-5mA			-0.8	V
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-50mA, I <sub>B</sub> =-5mA			-1.0	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =-10μA, I <sub>E</sub> =0	-400			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =-1mA, R <sub>BE</sub> =∞	-400			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I <sub>E</sub> =-10μA, I <sub>C</sub> =0	-5			V
Collector Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =–30V, f=1MHz		5		pF
Reverse Transfer Capacitance	C <sub>re</sub>	V <sub>CB</sub> =–30V, f=1MHz		4		pF
Turn-ON Time	ton	See specified Test Circuit		0.25		μs
Turn-OFF Time	toff	See specified Test Circuit		5		μs

 $<sup>\</sup>mbox{\ast}$  : The 2SA1700 is classified by 50mA  $\mbox{h}_{FE}$  as follows :

60 D 120 100 E 200

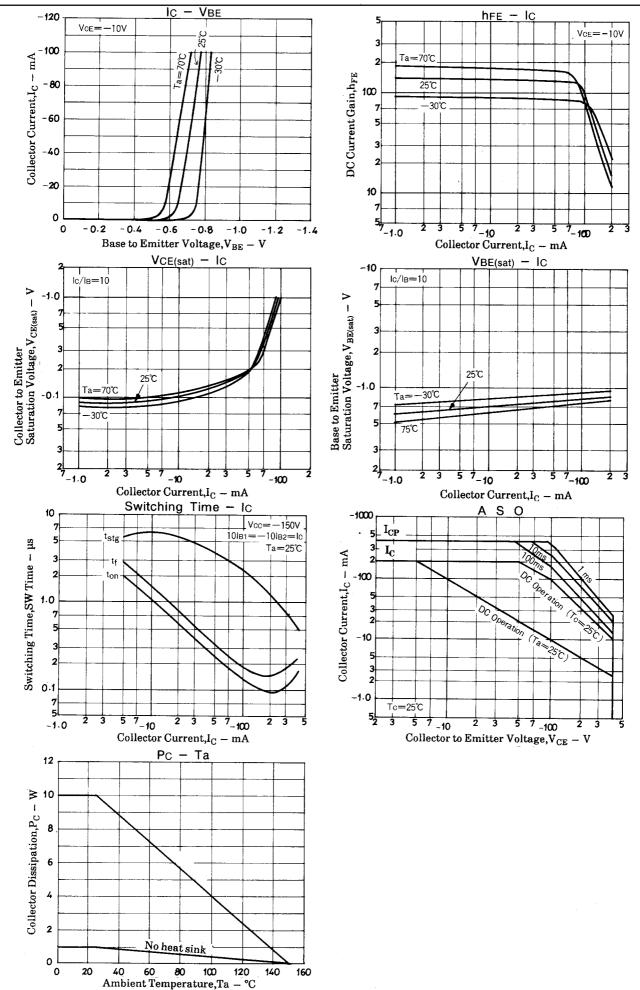
### **Switching Time Test Circuit**



 $-10l_{B1} = 10l_{B2} = l_{C} = -50mA$ 

 $R_L = 3k\Omega$ ,  $R_B = 200\Omega$  at  $I_C = -50mA$ 

Unit (resistance :  $\Omega$ , capacitance : F)



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